

## Product Overview

### NGTB30N60IHLWG: IGBT, Field Stop (FS), 30 A, 600 V

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for half bridge resonant applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

#### Features

- Low Saturation Voltage using Trench with Fieldstop Technology
- Low Switching Loss

#### Benefits

- Low Conduction Loss
- Reduces System Power Dissipation

#### Applications

- Half Bridge IH

#### End Products

- Inductive Heating Hobs

### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	$I_C$ Max (A)	$V_{CE(sat)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_T$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu$ s)	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co-Pack aged Diode	Package Type
NGTB30N60IHLWG	Pb-free Halide free	Active	600	30	1.8	1.2	0.28	-	400	23	130	-	-	250	Yes	TO-247-3

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